2114 Static RAMs

1024 X 4 N-MOS TTL IN/Out

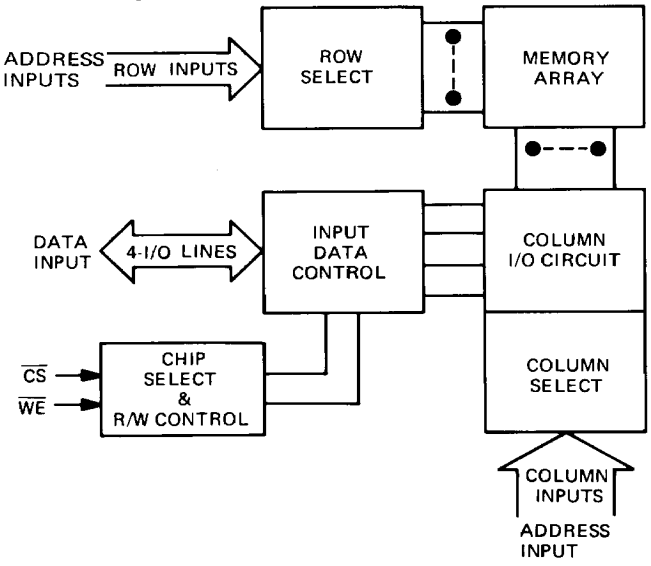
Features

- 1024 words x 4 bits
- Three access times (200, 300, and 450 nSec)
- Low power device—175 mW typical
- Standard power device—225 mW typical
- Common output bus
- Three-state output drivers
- Fully STATIC—no clock or refresh
- Single +5V power supply
- TTL compatible interface
- 18-pin ceramic, plastic or cerdip package

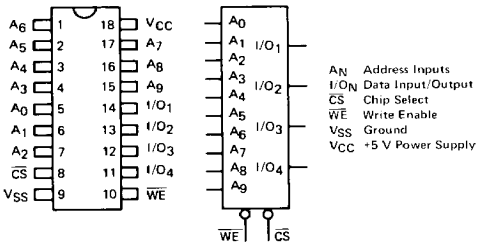
General Description

GTE Series 2114 RAMs are 1024 word x 4 bit static N-MOS Random Access Memories. These fully static memory cells require no external clocks, strobes or data refresh circuitry. TTL compatible Three-State output drivers allow the use of common I/O lines—ideally suited for microprocessor interfacing to a common I/O bus. A single +5V input is the only power supply requirement. Read/Write functions are controlled by the low state of Chip Select ($\overline{CS}$) and the concurrent *high* or *low* level of Write Enable ($\overline{WE}$) to initiate a Read or Write cycle respectively—with no pulse or edge triggering required. With $\overline{CS}$ high (STANDBY), a high impedance is reflected to the I/O bus—resulting in a no-load condition when non-selected. The 2114 is available in a choice of access times, power dissipation and packaging to meet your particular requirement.

Block Diagram



Pin Configuration and Logic Symbol



Truth Table

$\overline{CS}$	$\overline{WE}$	DI/DO	STATUS	MODE
H	Don't Care	High Z	Deselect	Standby
L	H	Data	Selected	Read
L	L	L	Selected	Write 0
L	L	H	Selected	Write 1

Specifications

	Max Access Time (nSec)	Min Cycle Time (nSec)	Max. I_{CC} Supply Current (mA)	Typ. I_{CC} Supply Current (mA)
2114-2	200	200	100	50
2114-3	300	300	100	50
2114-U	450	450	100	45
L2114-2	200	200	70	35
L2114-3	300	300	70	35
L2114-U	450	450	70	35
MIL-STD-883 Hi-Rel Device Available				

S-39

ORIG

002560

T-2560

GTE

Recommended Operating Conditions (T_{AMB} = 0° C to 70° C)

Parameter	Symbol	Min	Nom	Max	Units
Supply Voltage	V_{CC}	4.75	5.0	5.25	V
Input High Level	V_{IH}	2.0	–	5.25	V
Input Low Level	V_{IL}	−0.5	–	0.8	V

DC Electrical Characteristics (Full Operating Voltage and Temperature Range)

Characteristic	Symbol	Min	Typ	Max	Unit	Conditions
Input Leakage Current	I_{LI}	-10	–	+10	μA	V_{IN} = 0 to 5.25V
I/O Leakage Current	I_{LO}	-10	–	+10	μA	$V_{I/O}$ = 0.4 to 5.25V, CS = 2.4V
Output Voltage High	V_{OH}	2.4	–	–	V	I_O = -1.0 mA
Output Voltage Low	V_{OL}	–	–	0.4	V	I_O = 2.1 mA
Power Supply Current						
2114-2,3	I_{CC}	–	50	70	mA	T_{AMB} = 25°C
	I_{CC}	–	–	100	mA	T_{AMB} = 0°C to 70°C
L2114-2,3	I_{CC}	–	35	65	mA	T_{AMB} = 25°C
	I_{CC}	–	–	70	mA	T_{AMB} = 0°C to 70°C
2114-U	I_{CC}	–	45	75	mA	T_{AMB} = 25°C
	I_{CC}	–	65	100	mA	T_{AMB} = 0°C to 70°C
L2114-U	I_{CC}	–	35	45	mA	T_{AMB} = 25°C
	I_{CC}	–	40	70	mA	T_{AMB} = 0°C to 70°C

Read Cycle — AC Characteristics (Full Operating Voltage and Temperature Range)

		2114-2, L2114-2		2114-3, L2114-3		2114-U, L2114-U		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit
Read Cycle Time	T_{RC}	200	∞	300	∞	450	∞	nS
Access Time	T_A	–	200	–	300	–	450	nS
Chip Select-to-Output, Valid	T_{CO}	–	70	–	100	–	120	nS
Chip Select-to-Output, Active	T_{CX}	20	–	20	–	20	–	nS
Output Hold After Address Change	T_{OHA}	50	–	50	–	50	–	nS
Output Disable After Chip Deselection	T_{OTD}	–	60	–	80	–	100	nS

Write Cycle — AC Characteristics (Full Operating Voltage and Temperature Range)

		2114-2, L2114-2		2114-3, L2114-3		2114-U, L2114-U		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit
Write Cycle Time	T_{WC}	200	∞	300	∞	450	∞	nS
Write Pulse Width	T_W	120	–	150	–	200	–	nS
Write Recovery Time	T_{WR}	0	–	0	–	0	–	nS
Data Setup Time	T_{DW}	120	–	150	–	200	–	nS
Data Hold Time	T_{DH}	0	–	0	–	0	–	nS
Output Disable From Write or Chip Enable Time	T_{OTW}	–	60	–	80	–	100	nS

Capacitance

Parameter	Symbol	Typ	Max	Unit	Conditions
Input Capacitance	C_{IN}	4	5	pF	V_{IN} = 0V
Output Capacitance	$C_{I/O}$	4	5	pF	$V_{I/O}$

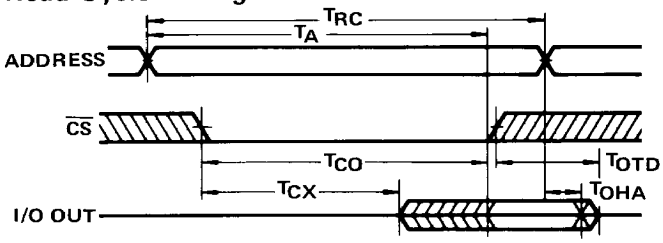
Absolute Maximum Ratings (See Note 1) (Referenced to GND)

RATING	VALUE	UNIT
Voltage on Any Pin With Respect to GND	-0.5 to +7.0	Vdc
Power Dissipation	1.0 (NOTE 2)	W
Operating Ambient Temperature Range (T_{AMB})	0 to +70	°C
Temperature Under Bias (T_{BIAS})	-10 to +80	°C
Storage Temperature (T_{STOR})	-65 to +150	°C
Current Into/From Output (I_O)	50	mA

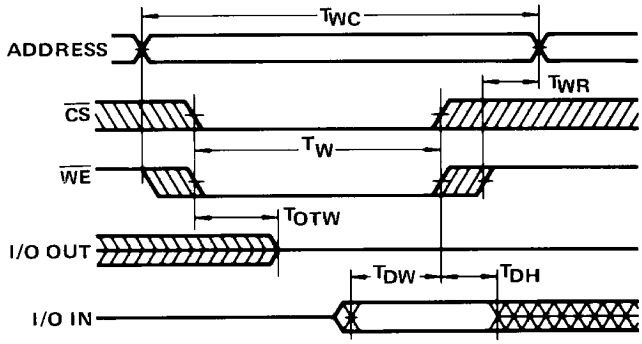
This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated values.

NOTE 1:Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPERATING CONDITIONS. Exposure to higher than recommended or maximum voltages for extended periods of time could affect device reliability.
NOTE2:At 25°C Ambient. Derate 13.5 mW/°C.

Read Cycle Timing



Write Cycle Timing



NOTES:
1. $\overline{WE}$ is high for a Read Cycle.
2. T_W is measured from the latter of $\overline{CS}$ or $\overline{WE}$ going low to the earlier of $\overline{CS}$ or $\overline{WE}$ going high.
3. $\overline{WE}$ or $\overline{CS}$ must be high prior to a write cycle to prevent an erroneous write during the address transitions.

Functional Description

The GTE Microcircuits 2114 is a 4096 bit static RAM, organized in a 1024 word by 4 bit configuration. Each word is selectively accessed by address lines A_0 through A_9, with data being read or written on common data input/output lines (I/O_1 through I/O_4), as controlled by the Chip Select ($\overline{CS}$) and Write Enable ($\overline{WE}$) functions.

Since no address setup time is required, data access is quite simple. With $\overline{WE}$ high and $\overline{CS}$ low, the array may be read by simply toggling the input address. Valid data output becomes available after time T_A, following each address change. However, should $\overline{CS}$ be used to control the read mode, valid data access time must be equal to or greater than T_A, but cannot occur earlier than T_{CO} from $\overline{CS}$ going low.

The write mode is enabled whenever $\overline{CS}$ and $\overline{WE}$ are both low. Stored data integrity is therefore preserved as long as either $\overline{CS}$ or $\overline{WE}$ is high. To write valid data, the address input may be applied simultaneously with the write enable ($\overline{CS}$ and $\overline{WE}$ both low), but must remain stable for the period T_{WC} while writing.

Possible write modes are as follows:
1. $\overline{CS}$ is held low. T_W is then defined by $\overline{WE}$ going from a high state to a low state and T_{WR} is defined by $\overline{WE}$ going from a low state to a high state.
2. $\overline{WE}$ is held low. $\overline{CS}$ going low is then used to define T_W. $\overline{CS}$ going high is used to define T_{WR}.
3. $\overline{CS}$ and $\overline{WE}$ are both used. T_W timing is defined by the latter of $\overline{CS}$ or $\overline{WE}$ going low, and T_{WR} timing is determined by the earlier of $\overline{CS}$ or $\overline{WE}$ going high.

The address must remain stable for the full Write cycle. However, data inputs are not required to remain stable for the full cycle. The correct logic level will be entered as long as input data is stable for the time period T_{DW} during the write cycle.

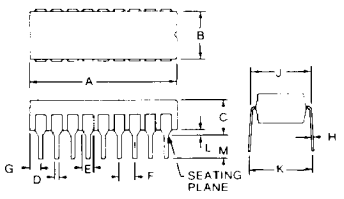
Functional Notes:

1. T_{AW} is measured from the latter of $\overline{CS}$ or $\overline{WE}$ going low.
2. T_W is measured from the latter of $\overline{CS}$ or $\overline{WE}$ going low, to the earlier of $\overline{CS}$ or $\overline{WE}$ going high.
3. T_{WR} is measured from the earlier of $\overline{CS}$ or $\overline{WE}$ going high.
4. T_{DH} and T_{DW} are measured from the earlier of $\overline{CS}$ or $\overline{WE}$ going high.
5. T_{OTW} is measured from $\overline{WE}$ going low or $\overline{CS}$ going high, whichever occurs first.
6. Timing diagrams are based on loading to simulate the capacitive effect of twenty (20) additional outputs connected in parallel (100 pF) plus the current loading affect of one TTL input load.
7. Input pulse levels are 0.8 volts for logic low, to 2.0 volts for logic high.
8. Input rise and fall times are of equal value (10 nS).
9. Timing is measured from the 1.5 volt level whether the level is going high or low.
10. Each I/O line is a high impedance during the write mode, or when $\overline{CS}$ is high. Inputs always represent a high impedance.

GTE 2114 Static RAMs 1024 x 4 N-MOS TTL In/Out

Packaging Dimensions

TYPICAL OUTLINE DRAWING



"B" PLASTIC PACKAGE				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	21.590	23.622	0.850	0.930
B	6.096	7.493	0.240	0.295
C	–	5.588	–	0.210
D	0.381	0.584	0.015	0.023
E	1.143	1.778	0.045	0.070
F	2.286	2.794	0.090	0.110
G	0.635	2.159	0.025	0.085
H	0.203	0.305	0.008	0.012
J	7.366	8.255	0.290	0.325
K	7.366	10.414	0.290	0.410
L	0.508	1.278	0.020	0.050
M	2.540	4.191	0.100	0.165

"A" CERAMIC PACKAGE				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	22.606	23.114	0.890	0.910
B	7.061	7.569	0.278	0.298
C	–	4.826	–	0.190
D	0.381	0.584	0.015	0.023
E	1.016	1.778	0.040	0.070
F	2.286	2.794	0.090	0.110
G	0.762	1.778	0.030	0.070
H	0.203	0.305	0.008	0.012
J	7.620	8.077	0.300	0.318
K	7.620 REF		0.300 REF	
L	0.635	1.651	0.025	0.065
M	2.540	3.810	0.100	0.150

"E" CERDIP PACKAGE				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	22.402	23.495	0.882	0.925
B	–	7.874	–	0.310
C	–	4.826	–	0.190
D	0.381	0.584	0.015	0.023
E	1.143	1.651	0.045	0.065
F	2.286	2.794	0.090	0.110
G	0.381	1.270	0.015	0.050
H	0.203	0.305	0.008	0.012
J	7.366	8.128	0.290	0.320
K	8.255	9.906	0.325	0.390
L	0.381	1.016	0.015	0.040
M	2.540	3.937	0.100	0.155

Ordering Information

DEVICE	ACCESS TIME	MAXIMUM POWER DISSIPATION	PACKAGE	TEMP. RANGE
2114-2CA	200 nS	525 mW	18-pin Ceramic	0°C to 70°C
2114-2CB	200 nS	525 mW	18-pin Plastic	0°C to 70°C
2114-2CE	200 nS	525 mW	18-pin Cerdip	0°C to 70°C
L2114-2CA	200 nS	368 mW	18-pin Ceramic	0°C to 70°C
L2114-2CB	200 nS	368 mW	18-pin Plastic	0°C to 70°C
L2114-2CE	200 nS	368 mW	18-pin Cerdip	0°C to 70°C
2114-3CA	300 nS	525 mW	18-pin Ceramic	0°C to 70°C
2114-3CB	300 nS	525 mW	18-pin Plastic	0°C to 70°C
2114-3CE	300 nS	525 mW	18-pin Cerdip	0°C to 70°C
L2114-3CA	300 nS	368 mW	18-pin Ceramic	0°C to 70°C
L2114-3CB	300 nS	368 mW	18-pin Plastic	0°C to 70°C
L2114-3CE	300 nS	368 mW	18-pin Cerdip	0°C to 70°C
2114-UCA	450 nS	525 mW	18-pin Ceramic	0°C to 70°C
2114-UCB	450 nS	525 mW	18-pin Plastic	0°C to 70°C
2114-UCE	450 nS	525 mW	18-pin Cerdip	0°C to 70°C
L2114-UCA	450 nS	315 mW	18-pin Ceramic	0°C to 70°C
L2114-UCB	450 nS	315 mW	18-pin Plastic	0°C to 70°C
L2114-UCE	450 nS	315 mW	18-pin Cerdip	0°C to 70°C

WARNING:

MOS CIRCUITS ARE SUBJECT TO DAMAGE FROM STATIC DISCHARGE

Internal static discharge circuits are provided to minimize part damage due to environmental static electrical charge build-ups. Industry established recommendations for handling MOS circuits include:

1. Ship and store product in conductive shipping tubes or in conductive foam plastic. Never ship or store product in non-conductive plastic containers or non-conductive plastic foam material.
2. Handle MOS parts only at conductive work stations.
3. Ground all assembly and repair tools.

Represented in your area by:

GTE Microcircuits products are stocked at more than 70 distributor locations throughout the U.S. For the name of your nearest distributor, call **Toll Free 800-526-6050, Ext. 1344**

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